	Application No.	Applicant(s)
Notice of Allowability	10/699,047	KIM, JI-YOUNG
	Examiner	Art Unit
	Khanh B. Duong	2822
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate communication is s	n this application. If not included unication will be mailed in due course. THIS
1. This communication is responsive to the election filed 4 Feb.	ebruary 2005.	
2. 🔀 The allowed claim(s) is/are <u>8-15</u> .		
3. The drawings filed on 30 October 2003 are accepted by the	ne Examiner.	
 4. Acknowledgment is made of a claim for foreign priority u a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received:	e been received. e been received in Applicatio	on No
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDON'THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be subminformal PATENT APPLICATION (PTO-152) which give		
 CORRECTED DRAWINGS (as "replacement sheets") mu (a) including changes required by the Notice of Draftsper 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in 	son's Patent Drawing Reviev - 's Amendment / Comment or 1.84(c)) should be written on the	in the Office action of he drawings in the front (not the back) of
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT		
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Si Paper No./ 08), 7. ⊠ Examiner's	formal Patent Application (PTO-152) ummary (PTO-413), 'Mail Date Amendment/Comment Statement of Reasons for Allowance
		AMIR ZADARIAN

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DETAILED ACTION

Election/Restrictions

Applicant's election without traverse of Group II (claims 8-15) in the reply filed on February 4, 2005 is acknowledged.

Priority

Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR.

1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

In the Title:

Please amend the title as follows: --METHOD OF FABRICATING A MOSFET HAVING A RECESSED CHANNEL--.

In the Claims:

Please cancel claims 1-7 and 16.

Allowable Subject Matter

Claims 8-15 are allowed.

The following is an examiner's statement of reasons for allowance: none of the prior art of record fairly shows or suggests all the process limitations as claimed.

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Specifically, regarding claim 8, none of the prior art of record discloses the following limitations in combination with other limitations: sequentially forming a gate conductive layer and a capping layer on the gate oxide layer so as to completely fill the recessed trench; forming a gate electrode that is overlapped by the gate conductive layer filling the recessed trench by patterning the capping layer and the gate conductive layer which rises over the semiconductor substrate to have a smaller critical dimension than that of the recessed trench; and forming a source/drain region by implanting impurity ions into the semiconductor substrate on both sides of the gate electrode.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

The following U.S. Patents disclose relevant teachings regarding MOSFETs having recessed channels: Hummler '213, Bryant '517, Durcan et al. '732 and Hummler '558.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khanh B. Duong whose telephone number is (571) 272-1836. The examiner can normally be reached on 10:00-6:30.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

KBD

AMIR ZARABIAN

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